

DESCRIPTION

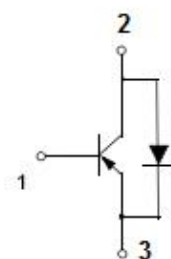
- High DC current gain
- Built-in a damper diode at E-C
- Lead formed for surface mount applications(NO suffix)
- Straight lead(IPAK, “-I” suffix)
- DPAK for surface mount applications
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

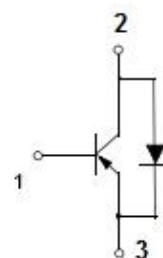
- Power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-5	A
I_C	Collector Current-Pulse	-10	A
P_C	Total Power Dissipation @ $T_a=25^\circ\text{C}$	1.4	W
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	12.5	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



PIN : 1 Base
2 Collector
3 Emitter
TO-251 Package



PIN : 1 Base
2 Collector
3 Emitter
TO-252 Package

isc Silicon PNP Power Transistor**KSH210****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

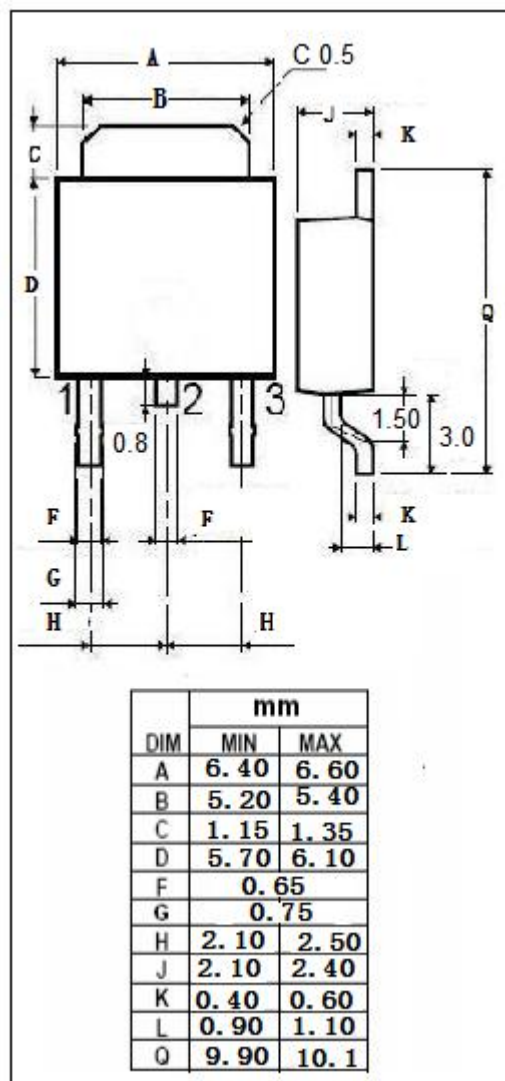
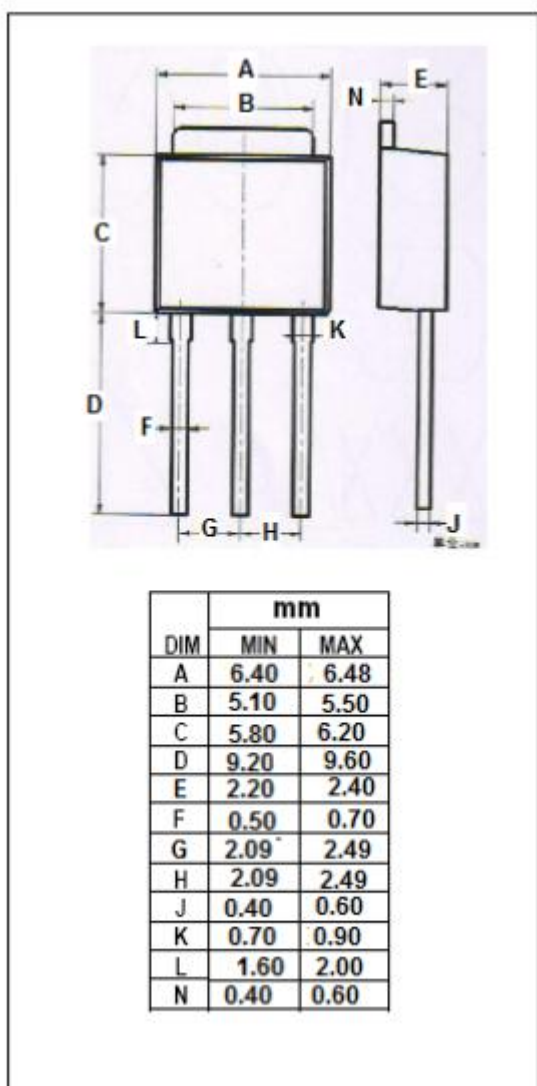
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-25			V
V _{CE(sat)-1*}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-0.3	V
V _{CE(sat)-2*}	Collector-Emitter Saturation Voltage	I _C = -2.0A; I _B = -200mA			-0.75	V
V _{CE(sat)-3*}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -1A			-1.8	V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = -5A; I _B = -1A			-2.5	V
V _{BE(on)*}	Base-Emitter On Voltage	I _C = -2A; V _{CE} =-1V			-1.6	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -40V; I _E = 0			-100	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -8V; I _C = 0			-100	nA
h _{FE1*}	DC Current Gain	I _C = -0.5A; V _{CE} = -1V	70			
h _{FE2*}	DC Current Gain	I _C = -2A; V _{CE} = -1V	45		180	
h _{FE3*}	DC Current Gain	I _C = -5A; V _{CE} = -2V	10			
f _T	Current-Gain—Bandwidth Product	I _C = -0.1A; V _{CE} = -10V		65		MHz
Cob	Collector output capacitance	V _{CB} =-10V, I _E =0, f=1MHz		120		pF

*:Pulse test PW≤300us,duty cycles≤2%

isc Silicon PNP Power Transistor

KSH210

Outline Drawing



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